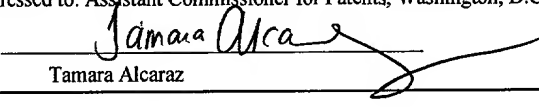


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Tamara Alcaraz

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the application of:

Masaaki KATOH

Serial No.: To Be Assigned

Filing Date: Herewith

For: LIGHT-EMITTING DIODE AND ITS
MANUFACTURING METHOD

Examiner: To Be Assigned

Group Art Unit: To Be Assigned

PRELIMINARY AMENDMENT

Box: PATENT APPLICATION
Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Prior to examination on the merits, applicant respectfully requests that the following amendment be entered.

AMENDMENTS

In the Specification:

On page 1, under BACKGROUND OF THE INVENTION, please insert the following paragraph:

--CROSS-REFERENCE TO RELATED APPLICATIONS

This application claims priority to Japanese Patent Application Number 2001-050558 filed February 26, 2001, and Japanese Patent Application Number 2002-41913 filed February 19, 2002, the contents of which are incorporated herein by reference in their entireties.--

In the Claims:

Please amend claims 4, 6, 8, and 10 as follows:

Please add new claims 12-27.

4. (Amended) A light-emitting diode claimed in Claim 1, wherein the light reflecting layer is formed of a metal thin film.
6. (Amended) A light-emitting diode claimed in Claim 4, wherein the metal thin film is formed of an Ni vapor-deposition film.
8. (Amended) A light-emitting diode claimed in Claim 1, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.
10. (Amended) A light-emitting diode claimed in Claim 1, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

Please add new claims 12-27

12. (New) A light-emitting diode claimed in Claim 2, wherein the light reflecting layer is formed of a metal thin film.

13. (New) A light-emitting diode claimed in Claim 5, wherein the metal thin film is formed of an Ni vapor-deposition film.

14. (New) A light-emitting diode claimed Claim 2, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

15. (New) A light-emitting diode claimed in Claim 3, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

16. (New) A light-emitting diode claimed in Claim 4, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

17. (New) A light-emitting diode claimed in Claim 5, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

18. (New) A light-emitting diode claimed in Claim 6, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

19. (New) A light-emitting diode claimed in Claim 7, wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

20. (New) A light-emitting diode claimed in Claim 2, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

21. (New) A light-emitting diode claimed in Claim 3, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

22. (New) A light-emitting diode claimed in Claim 4, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

23. (New) A light-emitting diode claimed in Claim 5, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

24. (New) A light-emitting diode claimed in Claim 6, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

25. (New) A light-emitting diode claimed in Claim 7, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

26. (New) A light-emitting diode claimed in Claim 8, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

27. (New) A light-emitting diode claimed in Claim 9, wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

REMARKS

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page is captioned "Version with markings to show changes made".

In the unlikely event that the transmittal letter is separated from this document and the Patent Office determines that an extension and/or other relief is required, applicant petitions for any required relief including extensions of time and authorizes the Assistant Commissioner to charge the cost of such petitions and/or other fees due in connection with the filing of this document to Deposit Account No. 03-1952 referencing docket no. 259052002900.

Respectfully submitted,

Dated: February 26, 2002

By:



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

In the Claims:

4. (Amended) A light-emitting diode claimed in Claim 1[or 2], wherein the light reflecting layer is formed of a metal thin film.

6. (Amended) A light-emitting diode claimed in Claim 4 [or 5], wherein the metal thin film is formed of an Ni vapor-deposition film.

8. (Amended) A light-emitting diode claimed in [any one of] Claim[s] 1[to 7], wherein the Ni vapor-deposition film has a thickness of 100 nm or more.

10. (Amended) A light-emitting diode claimed in Claim[s] 1[to 9], wherein the substrate is formed of a transparent substrate transparent to color emitted by the light-emitting diode chip.

Claims 12-27 have been added